## Jordan D Greenlee

List of Publications by Year in descending order

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IODDAN D CREENLEE

#	Article	IF	CITATIONS
1	Structural, Optical, and Electrical Characterization of Monoclinic β-Ga2O3 Grown by MOVPE on Sapphire Substrates. Journal of Electronic Materials, 2016, 45, 2031-2037.	2.2	111
2	Substrate-Dependent Effects on the Response of AlGaN/GaN HEMTs to 2-MeV Proton Irradiation. IEEE Electron Device Letters, 2014, 35, 826-828.	3.9	78
3	Symmetric Multicycle Rapid Thermal Annealing: Enhanced Activation of Implanted Dopants in GaN. ECS Journal of Solid State Science and Technology, 2015, 4, P382-P386.	1.8	45
4	Selective p-type Doping of GaN:Si by Mg Ion Implantation and Multicycle Rapid Thermal Annealing. ECS Journal of Solid State Science and Technology, 2016, 5, P124-P127.	1.8	43
5	Multicycle rapid thermal annealing optimization of Mg-implanted GaN: Evolution of surface, optical, and structural properties. Journal of Applied Physics, 2014, 116, .	2.5	39
6	Observation and control of the surface kinetics of InGaN for the elimination of phase separation. Journal of Applied Physics, 2012, 112, .	2.5	38
7	Improved Vertical GaN Schottky Diodes with Ion Implanted Junction Termination Extension. ECS Journal of Solid State Science and Technology, 2016, 5, Q176-Q178.	1.8	35
8	Impact of Surface Passivation on the Dynamic ON-Resistance of Proton-Irradiated AlGaN/GaN HEMTs. IEEE Electron Device Letters, 2016, 37, 545-548.	3.9	33
9	Degradation mechanisms of 2 MeV proton irradiated AlGaN/GaN HEMTs. Applied Physics Letters, 2015, 107, .	3.3	32
10	Characterization of an Mgâ€implanted GaN p–i–n diode. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2772-2775.	1.8	32
11	<i>In-situ</i> oxygen x-ray absorption spectroscopy investigation of the resistance modulation mechanism in LiNbO2 memristors. Applied Physics Letters, 2012, 100, .	3.3	31
12	Proton Radiation-Induced Void Formation in Ni/Au-Gated AlGaN/GaN HEMTs. IEEE Electron Device Letters, 2014, 35, 1194-1196.	3.9	30
13	Improvements in the Annealing of Mg Ion Implanted GaN and Related Devices. IEEE Transactions on Semiconductor Manufacturing, 2016, 29, 343-348.	1.7	30
14	Comparison of Interfacial and Bulk Ionic Motion in Analog Memristors. IEEE Transactions on Electron Devices, 2013, 60, 427-432.	3.0	28
15	Ultraviolet detector based on graphene/SiC heterojunction. Applied Physics Express, 2015, 8, 041301.	2.4	28
16	Halide based MBE of crystalline metals and oxides. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 155-160.	0.8	20
17	Spatial Mapping of Pristine and Irradiated AlGaN/GaN HEMTs With UV Single-Photon Absorption Single-Event Transient Technique. IEEE Transactions on Nuclear Science, 2016, 63, 1995-2001.	2.0	20
18	<i>In situ</i> investigation of the channel conductance of a Li1â^'xCoO2 (0 &lt; x &lt;â€9 ionic-electronic transistor. Applied Physics Letters, 2013, 102, .	‰Q. <u>5</u> )	18

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19	Radiation Effects on LiNbO\$_2\$ Memristors for Neuromorphic Computing Applications. IEEE Transactions on Nuclear Science, 2013, 60, 4555-4562.	2.0	15
20	Characterization of a selective AlN wet etchant. Applied Physics Express, 2015, 8, 036501.	2.4	15
21	Liquid Phase Electro-Epitaxy of Memristive LiNbO <sub>2</sub> Crystals. Crystal Growth and Design, 2014, 14, 2218-2222.	3.0	13
22	Comparison of AlN Encapsulants for Bulk GaN Multicycle Rapid Thermal Annealing. ECS Journal of Solid State Science and Technology, 2015, 4, P403-P407.	1.8	12
23	Defect reduction in MBE-grown AlN by multicycle rapid thermal annealing. Electronic Materials Letters, 2016, 12, 133-138.	2.2	12
24	Hyperspectral Electroluminescence Characterization of OFF-State Device Characteristics in Proton Irradiated High Voltage AlGaN/GaN HEMTs. ECS Journal of Solid State Science and Technology, 2016, 5, Q289-Q293.	1.8	11
25	Comparison of AlN encapsulants for high-temperature GaN annealing. Applied Physics Express, 2014, 7, 121003.	2.4	10
26	Degradation mechanisms of AlGaN/GaN HEMTs on sapphire, Si, and SiC substrates under proton irradiation. , 2014, , .		9
27	Thermal etching of nanocrystalline diamond films. Diamond and Related Materials, 2015, 59, 116-121.	3.9	9
28	Spatiotemporal drift-diffusion simulations of analog ionic memristors. Journal of Applied Physics, 2013, 114, .	2.5	8
29	Molecular beam epitaxy growth of niobium oxides by solid/liquid state oxygen source and lithium assisted metal-halide chemistry. Journal of Crystal Growth, 2015, 425, 225-229.	1.5	8
30	Temporary Bonding with Polydimethylglutarimide Based Lift Off Resist as a Layer Transfer Platform. ECS Journal of Solid State Science and Technology, 2015, 4, P190-P194.	1.8	7
31	UV Single-Photon Absorption Single-Event Transient Testing of Pristine and Irradiated AlGaN/GaN HEMTs. , 2015, , .		3
32	In situ Auger probe enabling epitaxy composition control of alloys by elemental surface analysis. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 03C126.	1.2	2
33	Process optimization of multicycle rapid thermal annealing of Mg-implanted GaN. , 2014, , .		1
34	Elimination of Basal Plane Dislocations in Epitaxial 4H-SiC via Multicycle Rapid Thermal Annealing. Materials Science Forum, 2015, 821-823, 297-302.	0.3	1